FAIRCHILD SEMICONDUCTOR®

August 2010

FDS86242

N-Channel PowerTrench® MOSFET

150 V, 4.1 A, 67 mΩ

Features

- Max $r_{DS(on)}$ = 67 mΩ at V_{GS} = 10 V, I_D = 4.1 A
- Max $r_{DS(on)}$ = 98 mΩ at V_{GS} = 6 V, I_D = 3.3 A
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability in a widely used surface mount package
- 100% UIL Tested
- RoHS Compliant

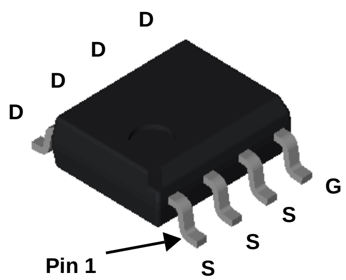
General Description

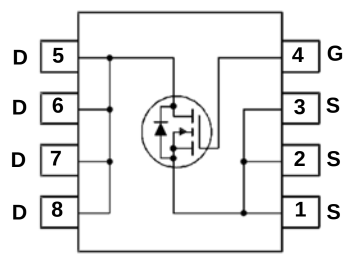
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been optimized for $r_{DS(on)}$, switching performance and ruggedness.

Applications

- DC/DC converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier

SO-8





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous	4.1	A
	-Pulsed	20	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	40	mJ
P_D	Power Dissipation T_C = 25 °C (Note 1)	5.0	W
	Power Dissipation T_A = 25 °C (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	25	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS86242	FDS86242	SO-8	13 ''	12 mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperatur Coefficient	I_D = 250 μA, referenced to 25 °C		104		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250 μA	2	3.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-10		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 4.1 A		56.3	67	mΩ
		V_{GS} = 6 V, I_D = 3.3 A		73.8	98	
		V_{GS} = 10 V, I_D = 4.1 A, T_J = 125 °C		107	126	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 4.1 A		11		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1MHz		570	760	pF
C_{oss}	Output Capacitance			64	85	pF
C_{rss}	Reverse Transfer Capacitance			2.9	5	pF
R_g	Gate Resistance			0.5		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 4.1 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		7.9	16	ns
t_r	Rise Time			1.5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			13	23	ns
t_f	Fall Time			2.8	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 75 V, I_D = 4.1 A		8.9	13	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 5 V		4.9	7	nC
Q_{gs}	Gate to Source Charge			3.0		nC
Q_{gd}	Gate to Drain "Miller" Charge			2.0		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 4.1 A (Note 2)		0.81	1.3	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)		0.77	1.2	
t_{rr}	Reverse Recovery Time	I_F = 4.1 A, di/dt = 100 A/μs		61	98	ns
Q_{rr}	Reverse Recovery Charge			71	114	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper.

b) 125 °C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25 °C, L = 1 mH, I_{AS} = 9 A, V_{DD} = 135 V, V_{GS} = 10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

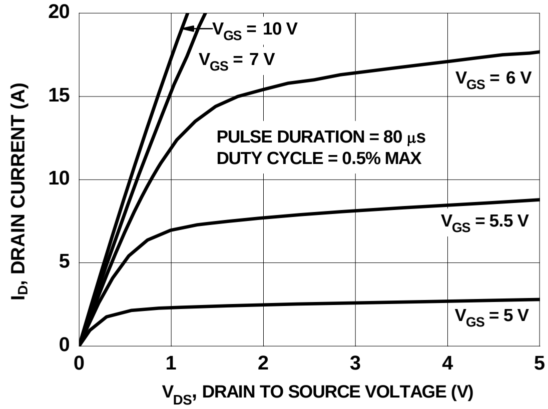


Figure 1. On-Region Characteristics

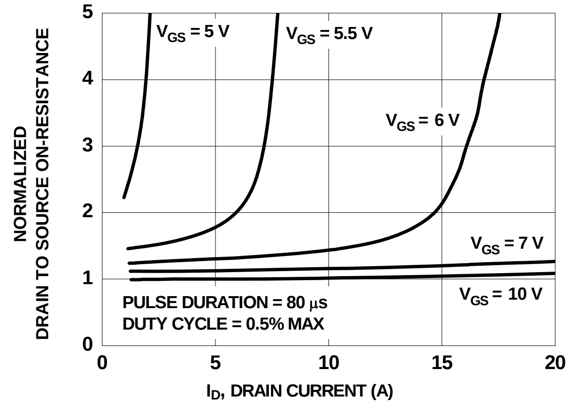


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

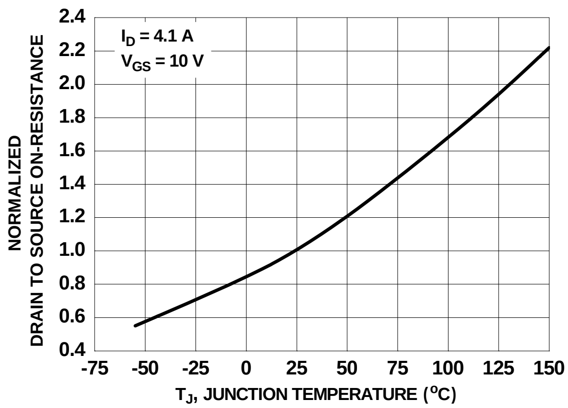


Figure 3. Normalized On-Resistance vs Junction Temperature

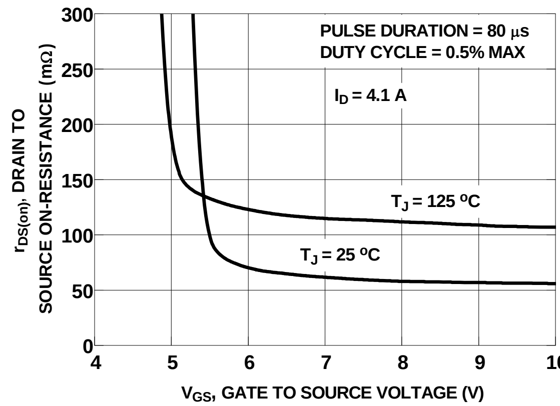


Figure 4. On-Resistance vs Gate to Source Voltage

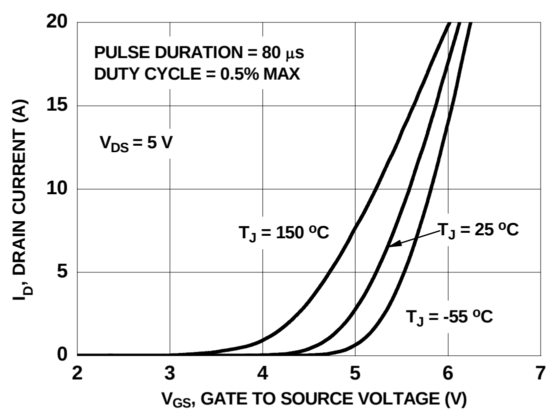


Figure 5. Transfer Characteristics

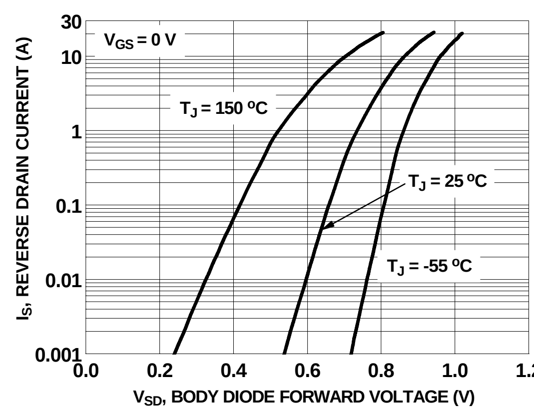


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

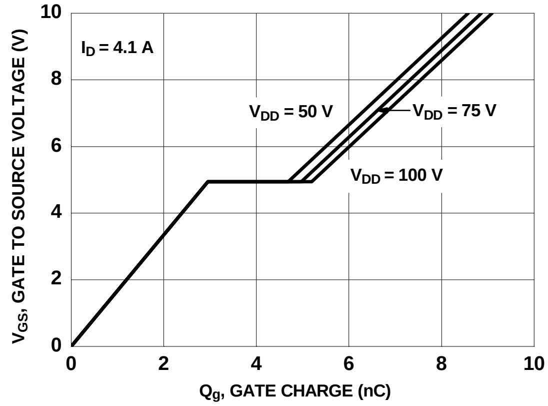


Figure 7. Gate Charge Characteristics

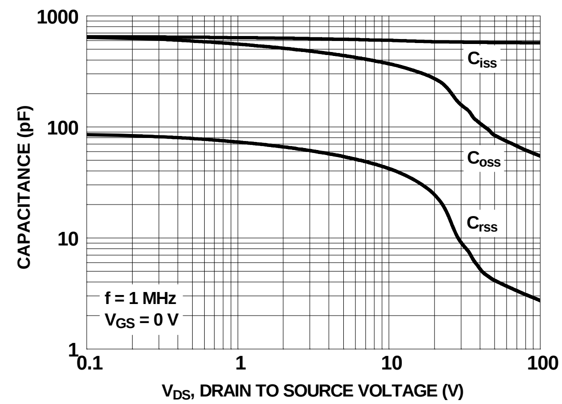


Figure 8. Capacitance vs Drain to Source Voltage

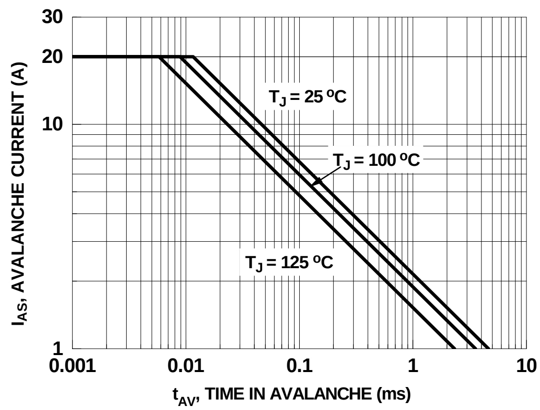


Figure 9. Unclamped Inductive Switching Capability

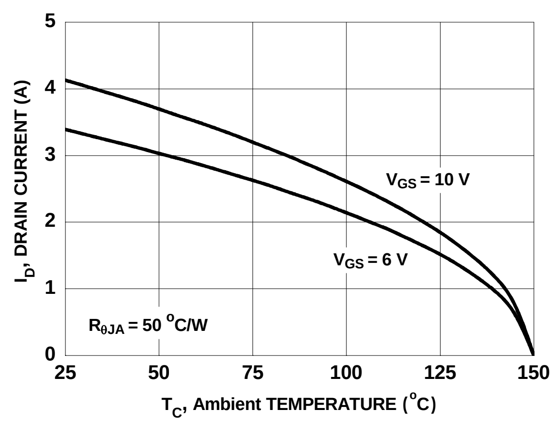


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

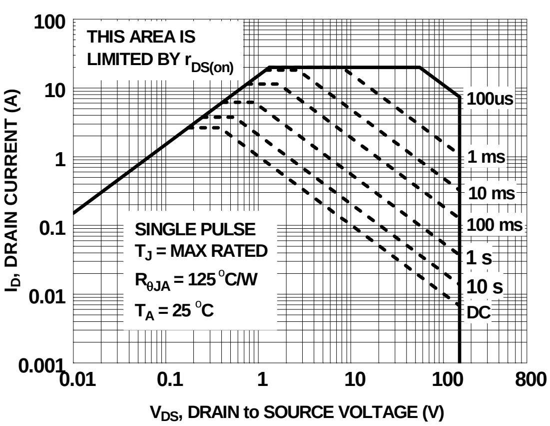


Figure 11. Forward Bias Safe Operating Area

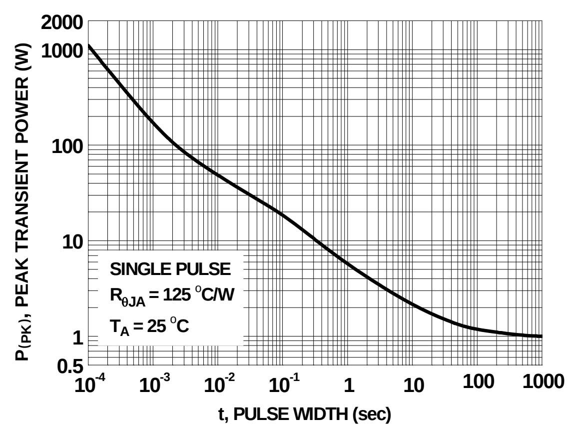


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

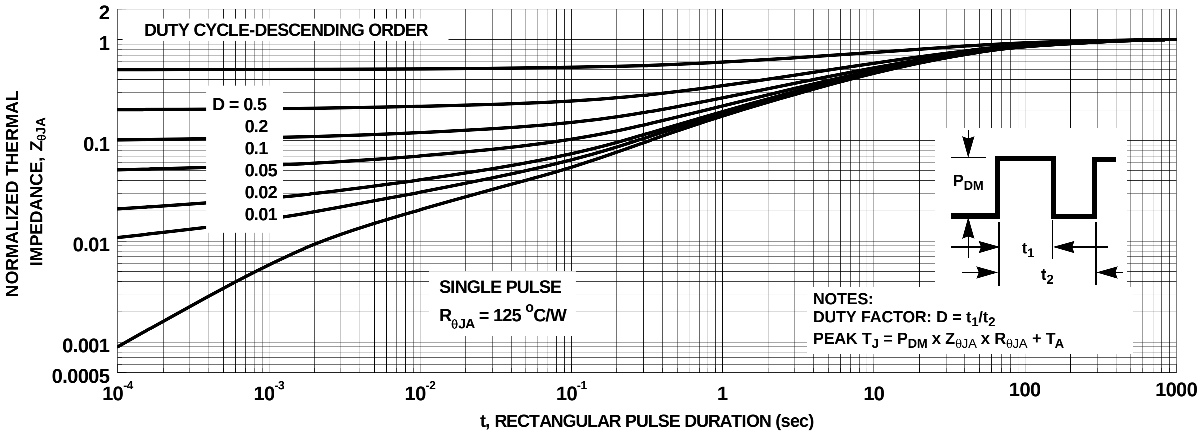


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

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